

E. Compound Semiconductors 분과

Room E

창의관 (B113)

일 시 : 2월 17일(금) 15:30-16:45

세션명 : [FE4-E] Electronics Devices and Processes III

좌 장 : 민병규(ETRI), 장태훈(LG전자)

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- FE4-E-1 15:30-15:45 **Demonstration of GaN MOSFET using Selectively Re-grown AlGaIn Layer on Source and Drain Regions**
저자: Dong-Seok Kim¹, Chul-Ho Won¹, Kyu-Il Jang¹, Sung-Dal Jung¹, Mi-Kyung Kwon¹, Hee-Sung Kang¹, Ki-Sik Im¹, Ki-Won Kim¹, Chung-Mo Yang¹, Jae-Joon Oh², Jong-Bong Ha², Jai-Kwang Shin², and Jung-Hee Lee¹
소속: ¹School of Electrical Engineering and Computer Science, Kyungpook National University, ²Samsung Advanced Institute of Technology
- FE4-E-2 15:45-16:00 **Improvement of Interfacial quality of Al₂O₃/GaN-MOSFETs by TMAH Treatment**
저자: Ki-Won Kim, Sung-Dal Jung, Mi-Kyung Kwon, Ki-Sik Im, Dong-Seok Kim, Hee-Sung Kang, and Jung-Hee Lee
소속: School of Electrical Engineering & Computer Science, Kyungpook National University
- FE4-E-3 16:00-16:15 **이중 전계판 구조를 가지는 고내압 AlGaIn/GaN-on-Si HFET에 대한 연구**
저자: 이호중, 이재길, 차호영
소속: 흥익대학교 전자전기공학부
- FE4-E-4 16:15-16:30 **Effects of Microstructural Changes on Electrical Properties of Ti/Al based Ohmic Contacts on N-face n-GaN**
저자: Buem Joon Kim, Yang Hee Song, Jun Ho Son, Hak Ki Yu, and Jong-Lam Lee
소속: Division of Advanced Materials Science and Department of Materials Science and Engineering, Pohang University of Science and Technology

FE4-E-5 16:30-16:45 **Reduction in Schottky Barrier Height of AlGaN-based SBD with In-situ Deposited Silicon Carbon Nitride (SiCN) Cap Layer**

저자: Jae-Hoon Lee¹, Young-Sun Kwak¹, Jae-Hyun Jeong¹, Heon-Bok Lee¹, Jong-Kyu Ryu¹, Ki-Se Kim¹, and Jung-Hee Lee²

소속: ¹Power Research Group, Samsung LED Co., Ltd., ²School of Electronic Engineering & Computer Science, Kyungpook National University